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Status	Product Specification
RF Communications	

NE/SE5539

High frequency operational amplifier

DESCRIPTION

The NE/SE5539 is a very wide bandwidth, high slew rate, monolithic operational amplifier for use in video amplifiers, RF amplifiers, and extremely high slew rate amplifiers.

Emitter-follower inputs provide a true differential input impedance device. Proper external compensation will allow design operation over a wide range of closed-loop gains, both inverting and non-inverting, to meet specific design requirements.

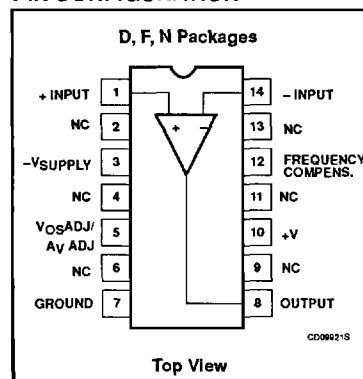
FEATURES

- Bandwidth
 - Unity gain – 350MHz
 - Full power – 48MHz
 - GBW – 1.2GHz at 17dB
- Slew rate: 600V/ μ s
- A_{VOL} : 52dB typical
- Low noise – 4nV/ $\sqrt{\text{Hz}}$ typical
- MIL-STD processing available

APPLICATIONS

- High speed datacom
- Video monitors & TV
- Satellite communications
- Image processing
- RF instrumentation & oscillators
- Magnetic storage
- Military communications

PIN CONFIGURATION



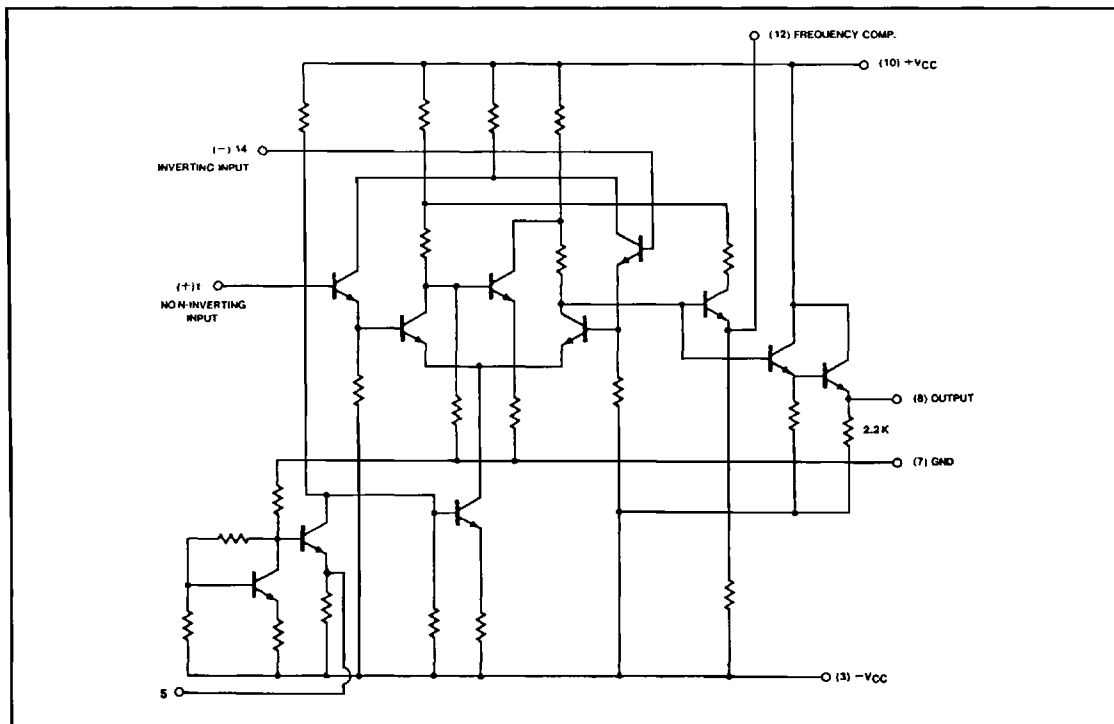
ORDERING INFORMATION

DESCRIPTION	TEMPERATURE RANGE	ORDER CODE
14-Pin Plastic DIP	0 to +70°C	NE5539N
14-Pin Plastic SO	0 to +70°C	NE5539D
14-Pin Cerdip	0 to +70°C	NE5539F
14-Pin Plastic DIP	-55 to +125°C	SE5539N
14-Pin Cerdip	-55 to +125°C	SE5539F

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EQUIVALENT SCHEMATIC



ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNITS
V_{CC}	Supply voltage	± 12	V
P_{DMAX}	Maximum power dissipation, $T_A = 25^\circ\text{C}$ (still-air) ² F package N package D package	1.17 1.45 0.99	W W W
T_A	Operating temperature range NE SE	0 to 70 -55 to +125	$^\circ\text{C}$ $^\circ\text{C}$
T_{STG}	Storage temperature range	-65 to +150	$^\circ\text{C}$
T_J	Max junction temperature	150	$^\circ\text{C}$
T_{SOLD}	Lead soldering temperature (10sec max)	+300	$^\circ\text{C}$

NOTES:

- Differential input voltage should not exceed 0.25V to prevent excessive input bias current and common-mode voltage 2.5V. These voltage limits may be exceeded if current is limited to less than 10mA.
- Derate above 25°C , at the following rates:
F package at $9.3\text{mW}/^\circ\text{C}$
N package at $11.6\text{mW}/^\circ\text{C}$
D package at $7.9\text{mW}/^\circ\text{C}$

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DC ELECTRICAL CHARACTERISTICS $V_{CC} = \pm 8V$, $T_A = 25^\circ C$; unless otherwise specified.

SYMBOL	PARAMETER	TEST CONDITIONS	SE5539			NE5539			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OUT}	Output voltage swing	$R_L = 150\Omega$ to GND and 470Ω to $-V_{CC}$ +Swing -Swing				+2.3 -1.7	+2.7 -2.2		V
V_{OUT}	Output voltage swing	$R_L = 25\Omega$ to GND Over temp	+2.3 -1.5	+3.0 -2.1					V
		$R_L = 25\Omega$ to GND $T_A = 25^\circ C$	+2.5 -2.0	+3.1 -2.7					V
I_{CC+}	Positive supply current	$V_O = 0$, $R_1 = \infty$, Over temp		14	18		2.8	3.5	mA
		$V_O = 0$, $R_1 = \infty$, $T_A = 25^\circ C$		14	17		14	18	mA
I_{CC-}	Negative supply current	$V_O = 0$, $R_1 = \infty$, Over temp		11	15		2.8	3.5	mA
		$V_O = 0$, $R_1 = \infty$, $T_A = 25^\circ C$		11	14		11	15	mA
PSRR	Power supply rejection ratio	$\Delta V_{CC} = \pm 1V$, Over temp		300	1000				$\mu V/V$
		$\Delta V_{CC} = \pm 1V$, $T_A = 25^\circ C$					200	1000	$\mu V/V$
A_{VOL}	Large signal voltage gain	$V_O = +2.3V$, $-1.7V$, $R_L = 150\Omega$ to GND, 470Ω to $-V_{CC}$				47	52	57	dB
A_{VOL}	Large signal voltage gain	$V_O = +2.3V$, $-1.7V$, $R_L = 2\Omega$ to GND, $T_A = 25^\circ C$				47	52	57	dB
A_{VOL}	Large signal voltage gain	$V_O = +2.5V$, $-2.0V$, $R_L = 2\Omega$ to GND, Over temp	46		60				dB
		$V_O = +2.5V$, $-2.0V$, $R_L = 2\Omega$ to GND, $T_A = 25^\circ C$	48	53	58				dB

DC ELECTRICAL CHARACTERISTICS $V_{CC} = \pm 6V$, $T_A = 25^\circ C$; unless otherwise specified.

SYMBOL	PARAMETER	TEST CONDITIONS	SE5539			UNITS
			MIN	TYP	MAX	
V_{OS}	Input offset voltage	Over temp		2	5	mV
		$T_A = 25^\circ C$		2	3	mV
I_{OS}	Input offset current	Over temp		0.1	3	μA
		$T_A = 25^\circ C$		0.1	1	μA
I_B	Input bias current	Over temp		5	20	μA
		$T_A = 25^\circ C$		4	10	μA
CMRR	Common-mode rejection ratio	$V_{CM} = \pm 1.3V$, $R_S = 100\Omega$	70	85		dB
I_{CC+}	Positive supply current	Over temp		11	14	mA
		$T_A = 25^\circ C$		11	13	mA
I_{CC-}	Negative supply current	Over temp		8	11	mA
		$T_A = 25^\circ C$		8	10	mA
PSRR	Power supply rejection ratio	$\Delta V_{CC} = \pm 1V$, Over temp		300	1000	$\mu V/V$
		$\Delta V_{CC} = \pm 1V$, $T_A = 25^\circ C$				$\mu V/V$

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DC ELECTRICAL CHARACTERISTICS $V_{CC} = \pm 6V$, $T_A = 25^\circ C$; unless otherwise specified.

SYMBOL	PARAMETER	TEST CONDITIONS	SE5539			UNITS
			MIN	TYP	MAX	
V_{OUT}	Output voltage swing	$R_L = 150\Omega$ to GND, 390Ω to $-V_{CC}$, Over temp +Swing -Swing	+1.4 -1.1	+2.0 -1.7		V
		$R_L = 150\Omega$ to GND, 390Ω to $-V_{CC}$, $T_A = 25^\circ C$ +Swing -Swing	+1.5 -1.4	+2.0 -1.8		mV

AC ELECTRICAL CHARACTERISTICS $V_{CC} = \pm 8V$, $R_L = 150\Omega$ to GND and 470Ω to $-V_{CC}$, unless otherwise specified.

SYMBOL	PARAMETER	TEST CONDITIONS	SE5539			NE5539			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
BW	Gain bandwidth product	$A_{CL} = 7$, $V_O = 0.1 V_{P-P}$		1200			1200		MHz
	Small signal bandwidth	$A_{CL} = 2$, $R_L = 150\Omega^1$		110			110		MHz
t_s	Settling time	$A_{CL} = 2$, $R_L = 150\Omega^1$		15			15		ns
SR	Slew rate	$A_{CL} = 2$, $R_L = 150\Omega^1$		600			600		V/ μs
t_{PD}	Propagation delay	$A_{CL} = 2$, $R_L = 150\Omega^1$		7			7		ns
	Full power response	$A_{CL} = 2$, $R_L = 150\Omega^1$		48			48		MHz
	Full power response	$A_v = 7$, $R_L = 150\Omega^1$		20			20		MHz
	Input noise voltage	$R_S = 50\Omega$, 1MHz		4			4		nV/ $\sqrt{Hz}$
	Input noise current	1MHz		6			6		pA/ $\sqrt{Hz}$

NOTES:

1. External compensation.

AC ELECTRICAL CHARACTERISTICS $V_{CC} = \pm 6V$, $R_L = 150\Omega$ to GND and 390Ω to $-V_{CC}$, unless otherwise specified.

SYMBOL	PARAMETER	TEST CONDITIONS	SE5539			UNITS
			MIN	TYP	MAX	
BW	Gain bandwidth product	$A_{CL} = 7$		700		MHz
	Small signal bandwidth	$A_{CL} = 2^1$		120		MHz
t_s	Settling time	$A_{CL} = 2^1$		23		ns
SR	Slew rate	$A_{CL} = 2^1$		330		V/ μs
t_{PD}	Propagation delay	$A_{CL} = 2^1$		4.5		ns
	Full power response	$A_{CL} = 2^1$		20		MHz

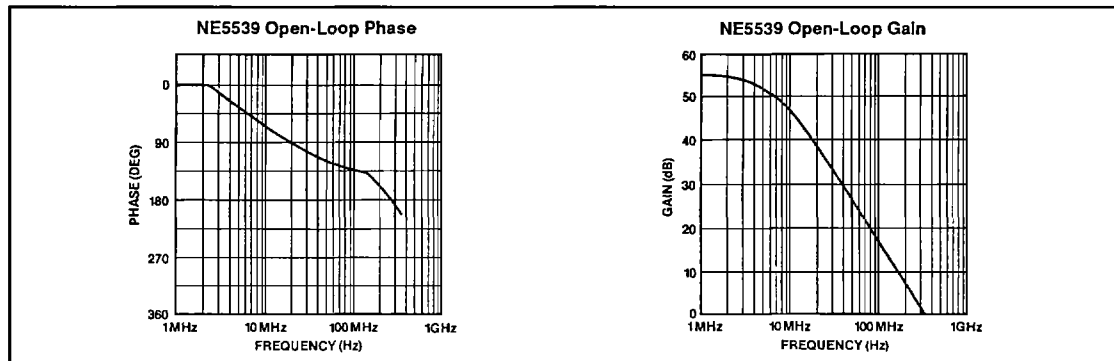
NOTES:

1. External compensation.

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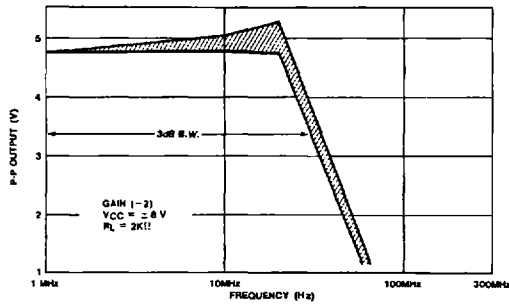
TYPICAL PERFORMANCE CURVES



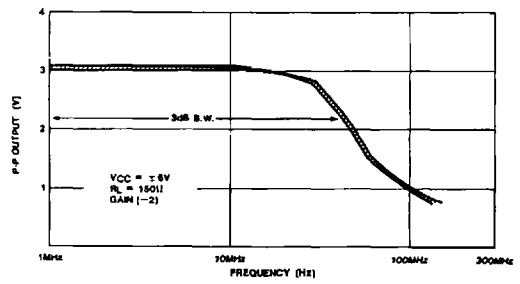
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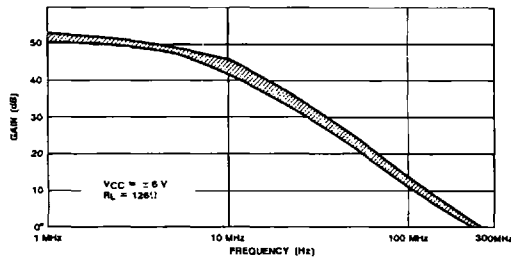
Power Bandwidth (SE)



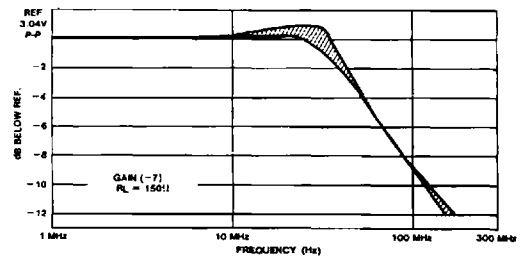
Power Bandwidth (NE)



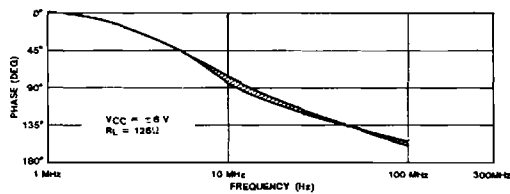
SE5539 Open-Loop Gain vs Frequency



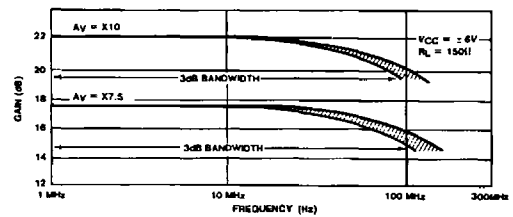
Power Bandwidth



SE5539 Open-Loop Phase vs Frequency



Gain Bandwidth Product vs Frequency

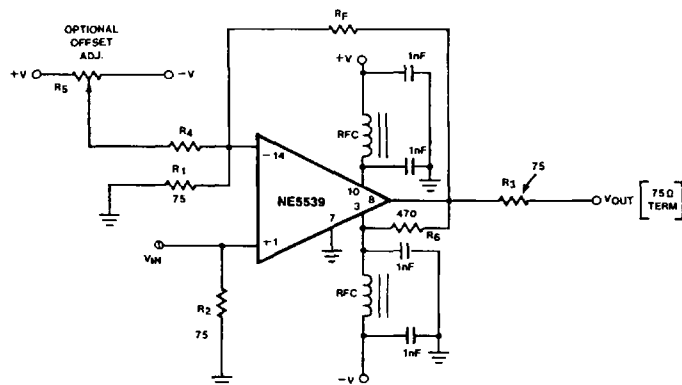


NOTE

Indicates typical distribution $-55^\circ\text{C} \leq T_A \leq 125^\circ\text{C}$

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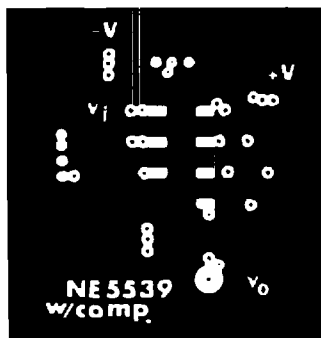
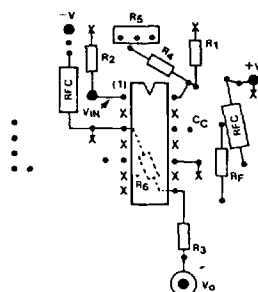
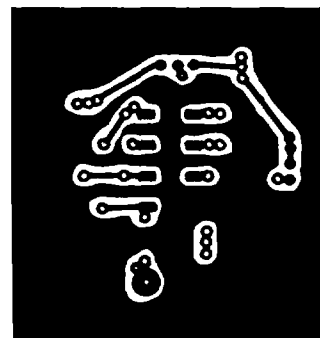
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NOTES:

R₁ = 75Ω 5% CARBONR₂ = 75Ω 5% CARBONR₃ = 75Ω 5% CARBONR₄ = 36k 5% CARBONR₅ = 20k TRIMPOT (CERMET)R_F = 1.5k (28dB GAIN)R_L = 470Ω 5% CARBON

RFC 3T # 26 BUSS WIRE ON
FERROXCUBE VK 200 09/3B CORE
BYPASS CAPACITORS
1nF CERAMIC
(MEPCO OR EQUIV.)

Top Plane Copper¹
(Component Side)Component Side
(Component Layout)Bottom Plane Copper¹

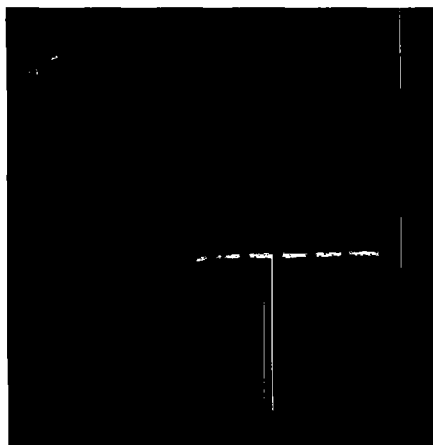
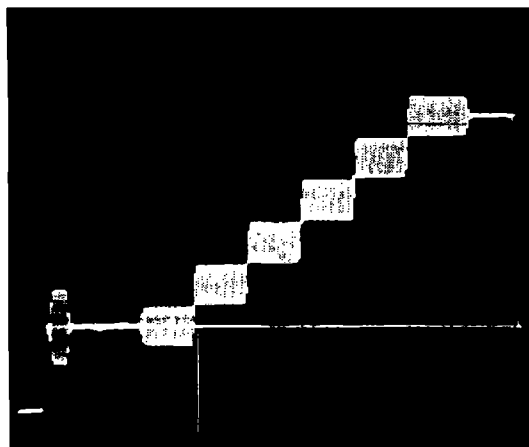
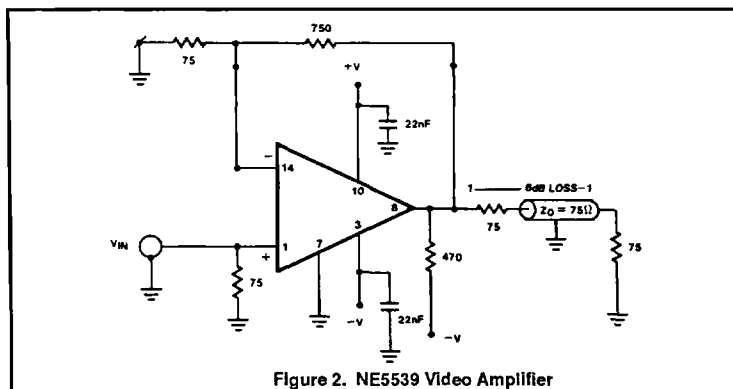
NOTE:

1. Bond edges of top and bottom ground plane copper.

Figure 1. 28dB Non-Inverting Amp Sample PC Layout

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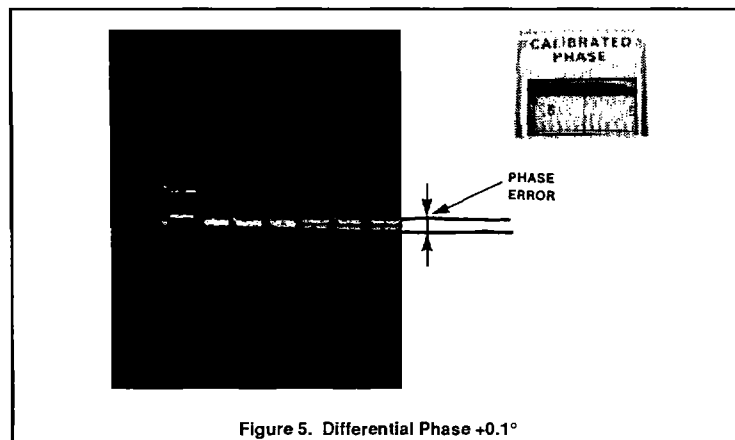
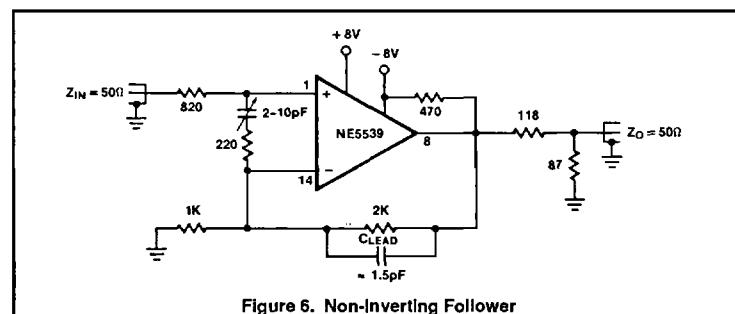
Figure 5. Differential Phase $+0.1^\circ$ 

Figure 6. Non-Inverting Follower

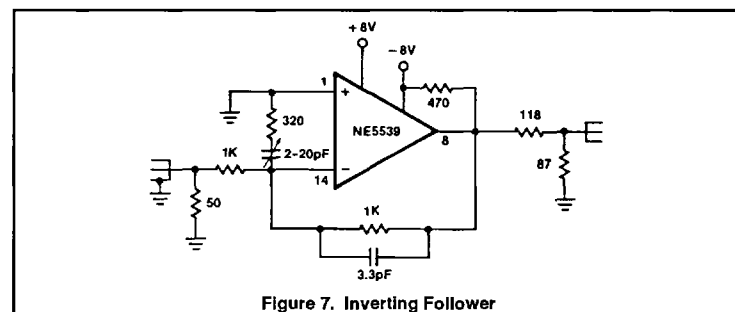


Figure 7. Inverting Follower